- 1 1. A method comprising:
- 2 forming an analog memory using a phase change
- 3 material.
- 1 2. The method of claim 1 including selectively
- 2 enabling either digital or analog data to be stored in said
- 3 memory.
- 1 3. The method of claim 1 including forming a phase
- 2 change material having a programmably variable resistance
- 3 for a plurality of cells.
- 1 4. The method of claim 3 including enabling said
- 2 cells to be addressably located along rows and columns.
- 1 5. The method of claim 1 including forming a phase
- 2 change material in a pore.
- 1 6. The method of claim 5 including forming a
- 2 selection device to enable the control of current through
- 3 said phase change material.
- 1 7. The method of claim 1 including enabling said
- 2 memory to store in a single cell one of at least three
- 3 different resistance values.

- 1 8. The method of claim 7 including enabling the
- 2 resistance of the cell to be set by varying the magnitude
- 3 of a programming current to the cell.
- 1 9. The method of claim 8 including enabling the
- 2 resistance of the cell to read and readjust using a
- 3 different programming current.
- 1 10. The method of claim 9 including enabling a
- 2 resistance to be set in said cell proportional to a voltage
- 3 or current characteristic to be stored.
- 1 11. A memory comprising:
- a phase change material; and
- a circuit to write analog data using said phase
- 4 change material.
- 1 12. The memory of claim 11 including a circuit to
- 2 selectively enable either digital or analog data to be
- 3 stored in said memory.
- 1 13. The memory of claim 11 wherein said phase change
- 2 material has a programmably variable resistance.
- 1 14. The memory of claim 13, said memory to store
- 2 digital and analog data.

- 1 15. The memory of claim 14 wherein said memory to
- 2 selectively store digital or analog data.
- 1 16. The memory of claim 15 including a circuit to
- 2 enable a user to select analog or digital data storage.
- 1 17. The memory of claim 16 including an analog read
- 2 sense amplifier, a digital read sense amplifier, an analog
- 3 write circuit, and a digital write circuit.
- 1 18. The memory of claim 11 including a substrate, an
- 2 insulator formed over said substrate, a pore defined in
- 3 said insulator, and a phase change material in said pore.
- 1 19. The memory of claim 11 including a plurality of
- 2 cells including a phase change material, said memory
- 3 including a plurality of conductive lines to selectively
- 4 enable access to said cells.
- 1 20. The memory of claim 19 wherein said phase change
- 2 material includes a chalcogenide.
- 1 21. A system comprising:
- 2 a processor;
- 3 a wireless interface coupled to said processor;
- 4 and

- a semiconductor memory coupled to said processor,
- 6 said memory including a phase change material and a circuit
- 7 to write analog data for storage using said phase change
- 8 material.
- 1 22. The memory of claim 21 including a circuit to
- 2 selectively enable either digital or analog data to be
- 3 stored in said memory.
- 1 23. The system of claim 21, said memory to store
- 2 digital and analog data.
- 1 24. The system of claim 23 wherein said memory to
- 2 selectively store digital or analog data.
- 1 25. The system of claim 24 including a circuit to
- 2 enable a user to select analog or digital data storage.